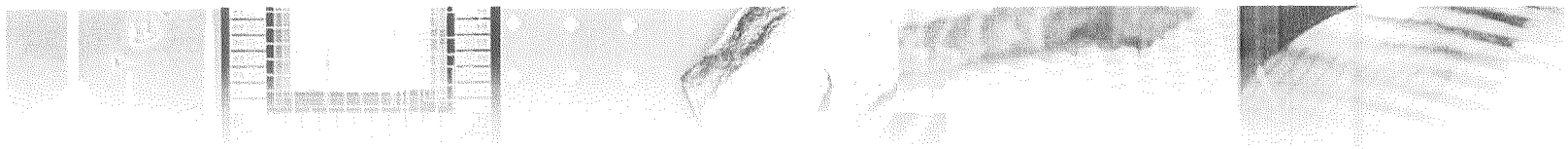
738



JNMO'08

12ièmes JOURNEES
NANO, MICRO
ET OTOELECTRONIQUE

du 3 au 6 Juin 2008
à l'ile d'Oléron

LASMEA

ims
BORDEAUX

Date limite de soumission des résumés : 16 mai 2008.

Date limite d'inscription : 23 mai 2008

Vendredi 6 Juin

Composants et intégration systèmes en optoélectronique (2)

8h30
Dries VAN THOURHOUT, INTEC Gent, Belgique
Photonic interconnect layer on CMOS by wafer scale integration.
9h00
Mathieu CARRAS, III-V Lab Palaiseau
Couplage entre les plasmons de surface et guides d'onde pour la réalisation de laser DFB QCL.
9h30
Jérôme TIGNON, ENS Paris
Micro-OPO.

10h00 PAUSE CAFE

Composants électroniques et intégration , micro-nano-électronique

10h30
Henry HAPPY et Thomas ZIMMER, IEMN Lille et IMS Bordeaux
Transistors hautes fréquences à base de nanotubes de carbone.
11h00
Yong JIN, LPN Marcoussis
Nanotransistor à effet de champ balistique avec un gain supérieur à 1 : de la physique mésoscopique à l'application réelle.
11h30
François FOREST, IES Montpellier
Intégration en électronique de puissance : enjeux scientifiques et technologiques.

12h00 CLOTURE DES JNMO'08

12h15 DEJEUNER

III-V Silicon heterogeneous integration for integrated transmitters and receivers

D. Van Thourhout[1], J. Van Campenhout[1], G. Roelkens, J. Brouckaert, P. Rojo-Romeo[2], P. Regreny[2], C. Seassal[2], P. Binetti[5], X.J.M. Leijtens[5], R. Nötzel[5], M.K.Smit[5], L. Di Cioccio[3], C. Lagahe[4], J.-M. Fedeli[3], R. Baets[1]

[1]Ghent University-IMEC, Sint-Pietersnieuwstraat 41, 9000 Ghent, Belgium (driesvt@intec.ugent.be)
[2]Institut des Nanotechnologies de Lyon (INL) (christian.seassal@ec-lyon.fr), [3]CEA-DRT/LETI(jean-marc.fedeli@cea.fr), [4]Tracit Technologies, (chrystelle.lagahe@tracit-tech.com), [5]Technical University Eindhoven(x.j.m.Leijtens@tue.nl)

Its high refractive index and low intrinsic losses make silicon an excellent material for realizing compact nanophotonic ICs operating at wavelengths in the telecom range. Moreover, the desired circuits can be realized with the most advanced equipment available, used also for the fabrication of high-end electronic circuits. Efficient light emission and amplification directly from silicon remains a bottleneck however. Therefore, in the context of the EU-project PICMOS, we developed an alternative approach, based on the heterogeneous integration of III-V epitaxial material and silicon nanophotonic circuits. Following fabrication and planarization of the latter, small unprocessed dies of InP-based epitaxial material are bonded on top. Next, the substrate of these dies is removed down to an etch stop layer. Finally the desired active optoelectronic devices are processed in the remaining III-V layers using waferscale processes. The critical alignment between the sources and the underlying nanophotonic circuits is ensured through accurate lithography. Based on this process we demonstrated electrically injected microdisk lasers coupled to silicon wire waveguides. They were operating under continuous wave operation and had a threshold current below 0.6mA (for a 7.5um disk diameter). Using a similar integration process we also demonstrated several types of InGaAs photodetectors with high efficiency. Linked to the microdisk lasers through a silicon wire waveguide, they could form the basis of very low optical interconnects for on-chip optical interconnect but also for high bandwidth transmitters and receivers in datacenters and other short off-chip optical interconnects. We also demonstrated Fabry-Perot type lasers with larger output powers that could be used as pump lasers for clock distribution circuits or for longer off-chip interconnects. In the talk we will present results from the EU FP6-project PICMOS and preliminary experiments from the FP7-project WADIMOS.